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(54) Title: MRAM ARRAY HAVING A PLURALITY OF MEMORY BANKS

(57) Abstract

An MRAM device has a new type of memory bank (10) that includes bit lines (21-24), a reference line (27) and digit lines (25, 26), on intersections of bit lines and digit lines a plurality of magnetic memory cells (15-18) are arrayed. Bit lines are formed on both sides of the reference line on a substrate. Since each bit line is fabricated closely to the reference line, each cell has substantially the same hysteresis characteristics, which allow the MRAM device to provide a steady operation mode.

